

Amendments to the claims:

This listing of claims will replace all prior versions and listing, of claims in the application:

Listing of Claims:

Claims 1-120 canceled.

Claim 121 (new): A method for fabricating semiconductor devices comprising:

a first separating step of cutting a substrate on which semiconductor elements having protruding electrodes are formed so that the semiconductor elements are separated from each other;

a resin sealing step of arranging the separated semiconductor elements on a base member and sealing a sealing resin so that a resin layer is formed;

a protruding electrode exposing step of exposing at least ends of the protruding electrodes from the resin layer; and

a second separating step, conducted after said protruding electrode exposing step, of cutting the resin layer together with the base member in positions between adjacent semiconductor elements, so that the semiconductor elements to which the resin layer is formed are separated from each other.

Claim 122 (new): A method for fabricating a semiconductor device comprising:

an electrode plate forming step of forming a pattern on a metallic base so that an electrode plate is formed;

a chip mounting step of mounting semiconductor elements on the electrode plate and electrically connecting the semiconductor elements thereto;

a sealing resin forming step of forming a sealing resin which seals the semiconductor

elements and the electrode plate; and

a cutting step of cutting the sealing resin and the electrode plate at boundaries between adjacent ones of the semiconductor elements so that the semiconductor devices are separated from each other,

wherein said sealing resin forming step is conducted by providing a film between said electrode plate and a mold.

Claim 123 (new): The method for fabricating the semiconductor device as claimed in claim 122, wherein the pattern is formed in the electrode plate forming step by etching or press processing.

Claim 124 (new): The method for fabricating the semiconductor device as claimed in claim 122, wherein the semiconductor elements are mounted, in the chip mounting step, on the electrode plate in a flip-chip bonding formation.

Claim 125 (new): The method for fabricating the semiconductor device as claimed in claim 122, wherein:

a chip attachment step of positioning the semiconductor elements on a heat radiating member and attaching the semiconductor elements thereto before the chip mounting step is executed; and

the semiconductor elements attached to the heat radiating member are mounted to the electrode plate in the chip mounting step.

Claim 126 (new): The method for fabricating the semiconductor device as claimed in claim 122, wherein:

protruding terminals protruding from the electrode plate are formed in the electrode plate forming step; and

the sealing resin is formed, in the sealing resin forming step, so as to expose the protruding terminals from the sealing resin.

Claim 127 (new): A semiconductor device comprising:

a semiconductor device main body having a semiconductor element having a surface on which protruding electrodes are directly formed, and a resin layer which is formed on the surface of the semiconductor element and seals the protruding electrodes except for ends thereof;

an interposer to which the semiconductor device main body is attached, a wiring pattern to which the semiconductor device main body is connected being formed on a base member of the interposer;

an anisotropic conductive film which has an adhesiveness and a conductivity in a pressed direction and is interposed between the semiconductor device main body and the interposer, the

anisotropic conductive film fixing the semiconductor device main body to the interposer and electrically connecting them; and

external connection terminals which are connected to the wiring pattern through holes formed in the base member and are arranged on a surface of the semiconductor device main body opposite to the surface on which the protruding electrodes are provided.

Claim 128 (new): The semiconductor device as claimed in claim 127 wherein an arrangement pitch for the protruding electrodes provided on the semiconductor device main body is equal to that for the external connection terminals provided on the interposer.

Claim 129 (new): The semiconductor device as claimed in claim 127, wherein an arrangement pitch for the external connection terminals provided on the interposer is greater than that for the protruding electrodes provided on the semiconductor device.

Claim 130 (new): The semiconductor device as claimed in claim 127 wherein there is provided an insulating member which is provided on the interposer and has holes located in positions facing the protruding electrodes.

Claim 131 (new): The semiconductor device as claimed in claim 127 wherein the interposer comprises a TAB (Tape Automated Bonding) tape.

Claim 132 (new): A method for fabricating a semiconductor device comprising:
a semiconductor device main body forming step of forming a semiconductor device main body having a semiconductor element having a surface on which protruding electrodes are directly formed, and a resin layer which is formed on the surface of the semiconductor element and seals the protruding electrodes except for ends thereof;

an interposer forming step of forming an interposer to which the semiconductor device main

body is attached, a wiring pattern to which the semiconductor device main body is connected being formed on a base member of the interposer;

a bonding step of bonding the semiconductor device main body and the interposer by an anisotropic conductive film which has an adhesiveness and a conductivity in a pressed direction, the anisotropic conductive film fixing the semiconductor device main body to the interposer and electrically connecting them; and

an external connection terminal forming step of forming external connection terminals which are connected to the wiring pattern through holes formed in the base member and are arranged on a surface of the semiconductor device main body opposite to the surface on which the protruding electrodes are provided.

Claim 133 (new): A semiconductor device comprising:

a semiconductor device main body having a semiconductor element having a surface on which protruding electrodes are directly formed, and a resin layer which is formed on the surface of the semiconductor element and seals the protruding electrodes except for ends thereof;

an interposer to which the semiconductor device main body is attached, a wiring pattern to which the semiconductor device main body is connected being formed on a base member of the interposer;

an adhesive which is provided between the semiconductor device main body and the interposer and which bonds the semiconductor device main body to the interposer;

a conductive member which electrically connects the semiconductor device main body and

the interposer; and

external connection terminals which are connected to the wiring pattern through holes formed in the base member and are arranged on a surface of the semiconductor device main body opposite to the surface on which the protruding electrodes are provided.

Claim 134 (new): The semiconductor device as claimed in claim 133 wherein the conductive member is a conductive paste.

Claim 135 (new): The semiconductor device as claimed in claim 133, wherein the conductive member comprises stud bumps.

Claim 136 (new): The semiconductor device as claimed in claim 133, wherein the conductive member comprises flying leads, which are integrally formed with the wiring pattern and bypasses the adhesive so as to be connected to the protruding electrodes.

Claim 137 (new): The semiconductor device as claimed in claim 136, wherein connections of the protruding electrodes and the flying leads are seal by resin.

Claim 138 (new): The semiconductor device as claimed in claim 133, wherein the conductive member comprises:

connection pins that are flexibly deformable and are located in positions corresponding to

those of the protruding electrodes; and

a positioning member positioning the connection pins,

upper ends of the connection pins being connected to the protruding electrodes of the semiconductor device, and lower ends thereof being connected to the external connection terminals.

Claim 139 (new): The semiconductor device as claimed in claim 138, wherein the positioning member is formed of a flexible member.

Claim 140 (new): A method for fabricating a semiconductor device comprising:

a semiconductor device main body forming step of forming a semiconductor device main body having a semiconductor element having a surface on which protruding electrodes are directly formed, and a resin layer which is formed on the surface of the semiconductor element and seals the protruding electrodes except for ends thereof;

an interposer forming step of forming an interposer to which the semiconductor device main body is attached, a wiring pattern to which the semiconductor device main body is connected being formed on a base member of the interposer;

a conductive member arranging step of arranging a conductive member to at least one of the semiconductor device main body and the interposer;

a bonding step of bonding the semiconductor device main body and the interposer by an adhesive and connecting them electrically; and

an external connection terminal forming step of forming external connection terminals which

are connected to the wiring pattern through holes formed in the base member and are arranged on a surface of the semiconductor device main body opposite to the surface on which the protruding electrodes are provided.